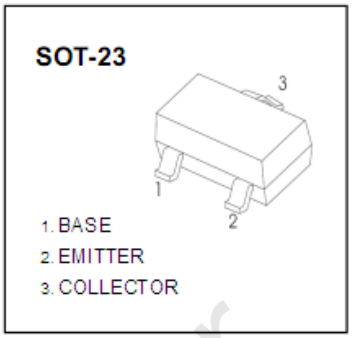
特点/Features：

I_C 电流大；

用途/Applications：

用于功率放大电路，与 SS8050 互补。

印章/Marking：Y2



极限参数/Absolute maximum ratings(Ta=25℃)

参数/Parameter	符号/ Symbol	数值/Value	单位/Unit
集电极-基极电压/Collector-Base Voltage	V_{CBO}	-40	V
集电极-发射极电压/Collector-Emitter Voltage	V_{CEO}	-25	V
发射极-基极电压/Emitter-Base Voltage	V_{EBO}	-5	V
集电极连续电流/Collector Current Continuous	I_C	-1.25～-1.5*	A
集电极耗散功率/Collector Power Dissipation	P_C	0.3	W
结温/Junction Temperature	Tj	150	℃
储存温度/Storage Temperature	Tstg	-55～150	℃

注：I_b在 100mA 时，I_C可在 1.5A 连续工作，I_b减小时，I_C最大连续工作电流会减小。

电性能参数/Electrical characteristics (Ta=25℃)

参数	符号	测试条件	最小值	最大值	单位
集电极-基极击穿电压	$V_{BR(CBO)}$	I_C=-100μA, I_E=0	-40		V
集电极-发射极击穿电压	$V_{BR(CEO)}$	I_C=-100μA, I_B=0	-25		V
发射极-基极击穿电压	$V_{BR(EBO)}$	I_E=-100μA, I_C=0	-5		V
集电极截止电流	I_{CBO}	V_{CB}=-40V, I_E=0		-0.1	μA
发射极截止电流	I_{EBO}	V_{EB}=-5V, I_C=0		-0.1	μA
集电极发射极穿透电流	I_{CEO}	V_{CE}=-20V, I_B=0		-0.1	μA
直流电流增益	$h_{FE(1)}$	V_{CE}=-1V, I_C=-100mA	120	400	
直流电流增益	$h_{FE(2)}$	V_{CE}=-1V, I_C=-800mA	40		
集电极-发射极饱和压降	$V_{CE(sat)}$	I_C=-800mA, I_B=-80mA		-0.5	V
基极-发射极饱和压降	$V_{BE(sat)}$	I_C=-800mA, I_B=-80mA		-1.2	V
基极-发射极导通压降	$V_{BE(ON)}$	I_C=-10mA, V_{CE}=-1V		-1	V
基极-发射极正向压降	V_{BEF}	I_B=-1A		-1.55	
特征频率	f_T	V_{CE}=-10V, I_C=-50mA, f=30MHz	100		MHz
输出电容	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz		20	pF

h_{FE} 分档/Classification of $h_{FE(1)}$

档位/Rank	L	H	J
范围/Range	120～200	200～350	300～400

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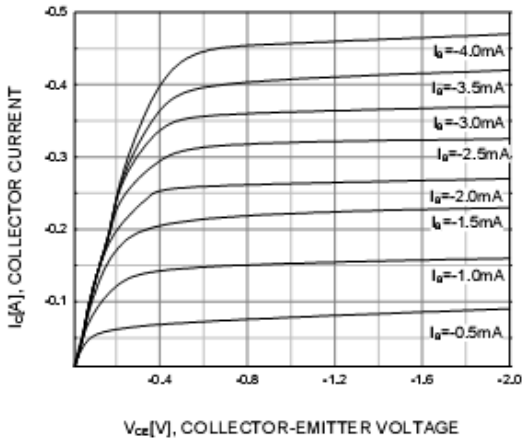
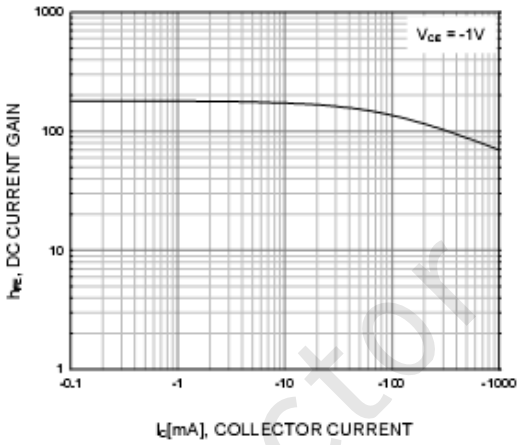
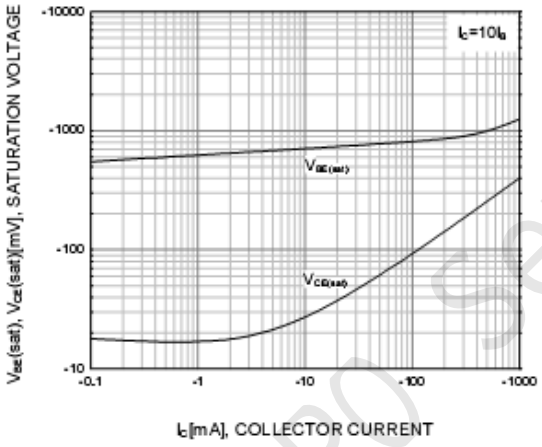
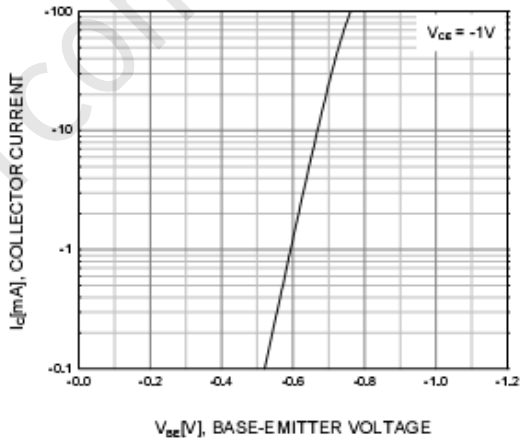
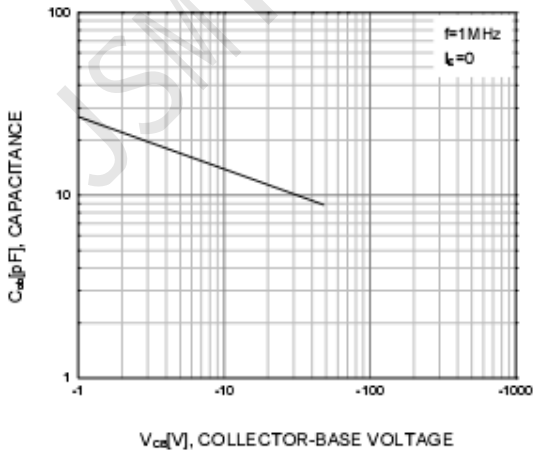
典型特性曲线图/Typical Characteristics

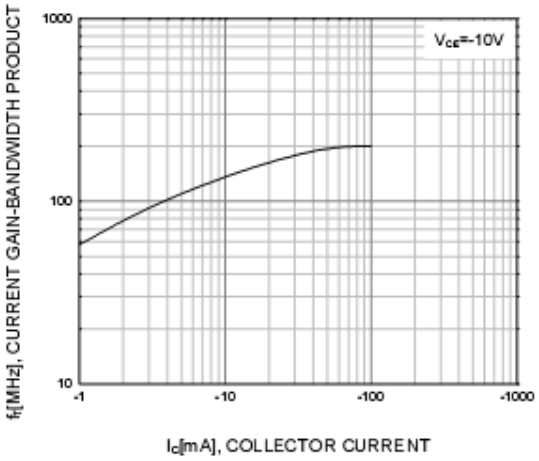












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